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MEDIA ADVISORY

Innovative Silicon Memory Expert, Dr. Wayne Ellis, to Speak at First Annual SOI Industry Consortium Members' Forum

SANTA CLARA, Calif., — November 10, 2008 — [Innovative Silicon, Inc.](http://www.innovative-silicon.com) (ISi), developer of the [Z-RAM](http://www.z-ram.com)® zero-capacitor floating body memory technology, today announced that Dr. Wayne Ellis, director of DRAM technology, is presenting at The First Annual SOI Industry Consortium Members' Forum. He is delivering a speech titled “SOI: Revolutionary Memory Solutions” at 4:00 p.m. on Tuesday, November 11th at TechMart in Santa Clara, CA.

The First Annual SOI Industry Consortium Members' Forum, taking place November 11 from 11:45 a.m. - 7:30 p.m., is open to anyone currently working for consortium member companies. For more information on the event see <http://www.soiconsortium.org>.

About the SOI Industry Consortium:

The SOI Industry Consortium is chartered with accelerating silicon-on-insulator (SOI) innovation into broad markets by promoting the benefits of SOI technology and reducing the barriers to adoption. Representing leaders spanning the entire electronics industry infrastructure, SOI Industry Consortium members include: AMD, Applied Materials, ARM, Cadence Design Systems, CEA-Leti, Chartered Semiconductor Manufacturing, Freescale Semiconductor, IBM, Innovative Silicon, KLA-Tencor, Lam Research, Magma Design, Nvidia, Samsung, Semico, Soitec, SEH Europe, STMicroelectronics, Symmid Semiconductor, Synopsys, TSMC, Tyndall Institute, UCL (University Catholique of Louvain) and UMC. Membership is open to all companies and institutions throughout the electronics industry. For more information, see <http://www.soiconsortium.org>

About Innovative Silicon

Innovative Silicon, Inc. (ISi) is the inventor and licensor of the Z-RAM® ultra-dense memory technology for stand-alone DRAM and embedded memory applications. Z-RAM is the world's lowest-cost semiconductor memory technology – simpler to manufacture than DRAM, and a fraction the size of SRAM. ISi and the Z-RAM technology have received numerous industry awards, including the World



Economic Forum's selection of ISi as a 2008 Technology Pioneer, and IEEE Spectrum Magazine's selection of Z-RAM as the 2007 "Emerging Technology Most Likely to Succeed." Z-RAM is a "Zero Capacitor," true single-transistor floating body memory that eliminates the complex capacitor found in today's DRAM technologies – a fundamental roadblock to Moore's Law of scaling. Z-RAM provides semiconductor manufacturers a solution for nanoscale manufacturing processes that can dramatically lower semiconductor costs. The Z-RAM memory technology has been licensed by Hynix Semiconductor for use in its DRAM chips, and by AMD for use in microprocessors. Since 2003, the company has closed three funding rounds totaling \$47 million, received over 30 patents on the technology, developed test chips in multiple technologies from 90nm to 32nm, and has established global R&D, engineering and support centers in Europe, Asia and North America. For more information see www.z-ram.com.

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